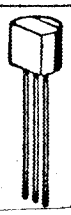
BC486 BC488 BC490

PNP SILICON PLANAR EPITAXIAL TRANSISTORS

MICRO ELECTRONICS

BC486, BC488 and **BC490** are **PNP** silicon planar epitaxial transistors designed for use as high voltage high current driver and output transistors.

CASE TO-92F



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ABSOLUTE MAXIMUM RATINGS

		BC486	BC488	BC490
Collector-Base Voltage	V_{CBO}	45V	60V	80V
Collector-Emitter Voltage	V_{CEO}	45V	60V	80V
Emitter-Base Voltage	V_{EBO}		5V	
Collector Current	I_C		1A	
Total Power Dissipation @ $T_A=25^\circ C$	P_{tot}		625mW	
@ $T_C=25^\circ C$			1.5W	
Operating Junction & Storage Temperature	Tj, Tstg		-55 to +150°C	

ELECTRICAL CHARACTERISTICS AT $T_A=25^\circ C$

PARAMETER		SYMBOL	MIN	TYP	MAX	UNIT	TEST CONDITIONS
Collector-Base Breakdown Voltage		BV_{CBO}	Note 1			V	I_C=0.1mA I_E=0
Collector-Emitter Breakdown Voltage		BV_{CEO}	Note 1			V	I_C=10mA I_B=0
Emitter-Base Breakdown Voltage		BV_{EBO}	Note 1			V	I_E=10μA I_C=0
Collector Cutoff Current		I_{CBO}			100	nA	$V_{CB}=V_{CBO}$ I_E=0
Collector-Emitter Saturation Voltage		$V_{CE(SAT)}$*			0.5	V	I_C=500mA I_B=50mA
Base-Emitter Saturation Voltage		$V_{BE(SAT)}$*			1.2	V	I_C=500mA I_B=50mA
D.C. Current Gain	All groups	H_{FE}*	40				I_C=10mA V_{CE}=2V
	All groups		60		400		I_C=100mA V_{CE}=2V
	Group L		60		150		I_C=100mA V_{CE}=2V
	Group A		100		250		I_C=100mA V_{CE}=2V
	Group B		160		400		I_C=100mA V_{CE}=2V
	All groups		15				I_C=1A V_{CE}=5V
Current Gain-Bandwidth Product		f_T		75		MHz	I_C=50mA V_{CE}=2V
Output Capacitance		Cob		12		pF	V_{CB}=10V I_E=0
Input Capacitance		Cib		85		pF	V_{BE}=2V I_C=0

Note 1 : equal to the values of the absolute maximum ratings.

* Pulse Test : Pulse Width=0.3ms, Duty Cycle=1%

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